DTGN15N120 www.din-tek.jp

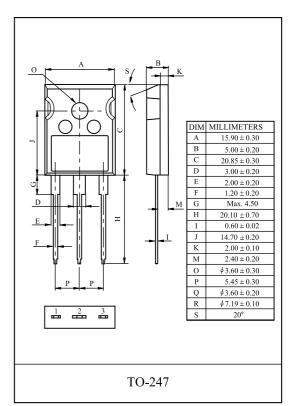
General Description

Din-Tek Field Stop Trench IGBTs offer low switching losses, high energy efficiency and short circuit ruggedness.

It is designed for applications such as motor control, uninterrupted power supplies(UPS), general inverters.

FEATURES

- · High speed switching
- \cdot High ruggedness, temperature stable behavior
- Short Circuit Withstand Times 10us
- · Extremely enhanced avalanche capability



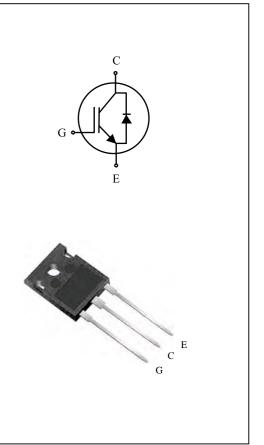
MAXIMUM RATING (Ta=25)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Collector-Emitter Voltage		V _{CES}	1200	V
Gate-Emitter Voltage	V _{GES}	± 20	V	
Collector Current	@T _C =25	- I _C	30	А
	@T _C =100	- ¹ C	15	А
Pulsed Collector Current	I _{CM} *	45	А	
Diode Continuous Forward Current @T _C =100		I _F	15	А
Diode Maximum Forward Current	I _{FM}	45	А	
	@T _C =25	- P _D	167	W
Maximum Power Dissipation	@T _C =100	I D	67	W
Maximum Junction Temperature		Tj	150	
Storage Temperature Range		T _{stg}	-55 to + 150	

*Repetitive rating : Pulse width limited by max. junction temperature

THERMAL CHARACTERISTIC

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Junction to Case (IGBT)	R _{thJC}	0.75	/W
Thermal Resistance, Junction to Case (DIODE)	R _{thJC}	2.0	/W
Thermal Resistance, Junction to Ambient	R _{thJA}	40	/W



ELECTRICAL CHARACTERISTICS (Ta=25)

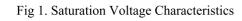
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Static				1		
Collector-Emitter Breakdown Voltage	BV _{CES}	$V_{GE}=0V$, $I_C=1.0mA$	1200	-	-	V
Collector Cut-off Current	I _{CES}	V _{GE} =0V, V _{CE} =1200V	-	-	1.0	mA
Gate Leakage Current	I _{GES}	$V_{CE}=0V, V_{GE}=\pm 20V$	-	-	±100	nA
Gate Threshold Voltage	V _{GE(th)}	$V_{GE} = V_{CE}$, $I_C = 15 \text{mA}$	4.5	5.5	7.0	V
		V _{GE} =15V, I _C =15A	-	2.0	2.4	V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	V_{GE} =15V, I_C =15A, T_C = 125	-	2.25	-	V
		V _{GE} =15V, I _C =30A	-	2.6	-	V
Dynamic				1		
Total Gate Charge	Qg		-	100	-	nC
Gate-Emitter Charge	Q _{ge}	V_{CC} =600V, V_{GE} =15V, I_{C} = 15A	-	15	-	nC
Gate-Collector Charge	Q _{gc}		-	50	-	nC
Turn-On Delay Time	t _{d(on)}	- V_{CC} =600V, I_{C} =15A, V_{GE} =15V, R_{G} =10 - Inductive Load, T_{C} = 25	-	30	-	ns
Rise Time	t _r		-	20	-	ns
Turn-Off Delay Time	t _{d(off)}		-	120	-	ns
Fall Time	t _f		-	110	-	ns
Turn-On Switching Loss	Eon		-	1.0	1.3	mJ
Turn-Off Switching Loss	E _{off}		-	0.55	0.75	mJ
Total Switching Loss	E _{ts}		-	1.55	2.05	mJ
Turn-On Delay Time	t _{d(on)}		-	30	-	ns
Rise Time	t _r		-	20	-	ns
Turn-Off Delay Time	t _{d(off)}		-	130	-	ns
Fall Time	t _f	V_{CC} =600V, I_C =15A, V_{GE} =15V, R_G =10 Inductive Load, T_C = 125	-	220	-	ns
Turn-On Switching Loss	Eon		-	1.15	-	mJ
Turn-Off Switching Loss	E _{off}		-	1.0	-	mJ
Total Switching Loss	E _{ts}		-	2.15	-	mJ
Input Capacitance	C _{ies}		-	1600	2080	pF
Ouput Capacitance	C _{oes}	V _{CE} =30V, V _{GE} =0V, f=1MHz	-	75	-	pF
Reverse Transfer Capacitance	C _{res}		-	45	-	pF
Short Circuit Withstand Time	t _{sc}	V _{CC} =600V, V _{GE} =15V, T _C =100	10	-	-	μs

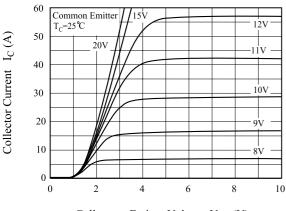
ELECTRICAL CHARACTERISTIC OF DIODE

CHARACTERISTIC	SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Diode Forward Voltage	V _F	$I_F = 15A$	T _C =25	-	2.4	3.0	- V
			T _C =125	-	2.5	-	
Diode Reverse Recovery Time	t _{rr}	I _F = 15A di/dt = 200A/ µs	T _C =25	-	115	-	ns
			T _C =125	-	140	-	
Diode Peak Reverse Recovery Current	I _{rr}		T _C =25	-	12.5	-	А
			T _C =125	-	14.0	-	А
Diode Reverse Recovery Charge	Q _{rr}		T _C =25	-	0.75	-	μC
			T _C =125	-	1.15	-	



Typical Performance Characteristics





Collector - Emitter Voltage $V_{CE}(V)$

Fig 3. Saturation Voltage vs. Case Temperature

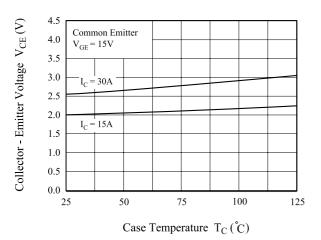
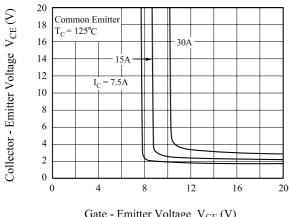
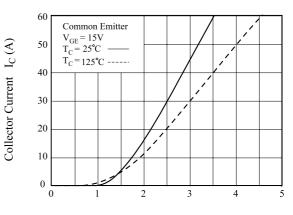


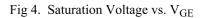
Fig 5. Saturation Voltage vs. VGE



Gate - Emitter Voltage V_{GE} (V)



Collector - Emitter Voltage V_{CE} (V)



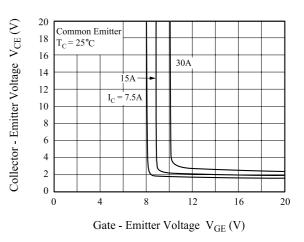
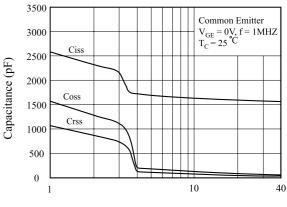


Fig 6. Capacitance Characteristics



Collector - Emitter Voltage $V_{CE}(V)$

Fig 2. Saturation Voltage Characteristics



Typical Performance Characteristics (Continued)

Fig 7. Turn-On Characteristics vs. Gate Resistance

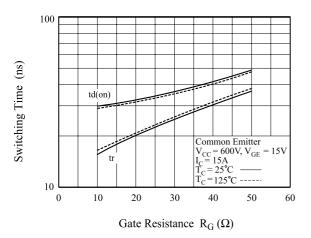


Fig 9. Switching Loss vs. Gate Resistance

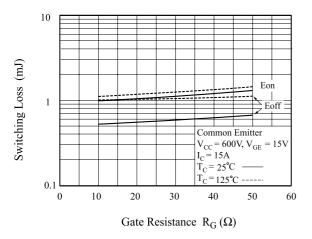
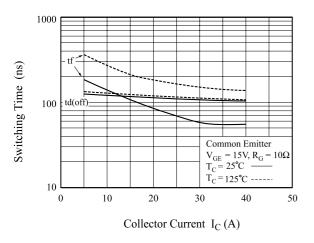
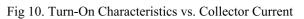


Fig 11. Turn-Off Characteristics vs. Collector Current



1000 td(off) Switching Time (ns) 100 Common Emitter $V_{CC} = 600V, V_{GE} = 15V$ $I_C = 15A$ $\tilde{T_C} = 25^{\circ}C$ $T_{C} = 125^{\circ}C$ -----10 10 0 20 30 40 50 60 Gate Resistance $R_{G}(\Omega)$



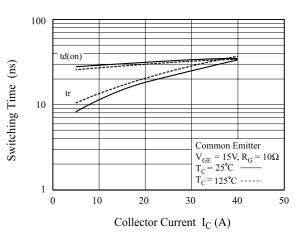


Fig 12. Switching Loss vs. Collector Current

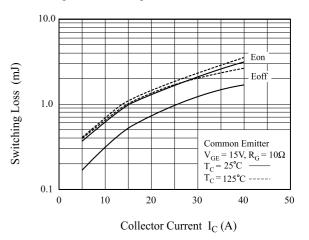
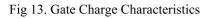
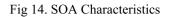


Fig 8. Turn-Off Characteristics vs. Gate Resistance

Typical Performance Characteristics (Continued)





DC

100

1000

ΗI

10

Collector-Emitter Voltage $V_{CE}(V)$

100.00

10.00

1.00

0.10

0.01

0.1

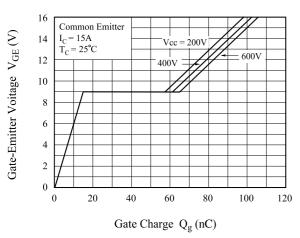
Collector Current I_C (A)

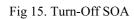
++++++ Single nonrepetitive pulse

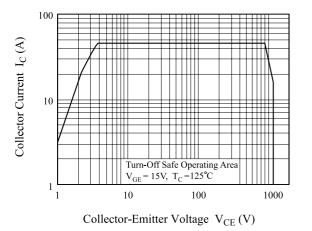
 $T_c = 25^{\circ}C$ Curves must be derated

linearly with increase in temperature

1







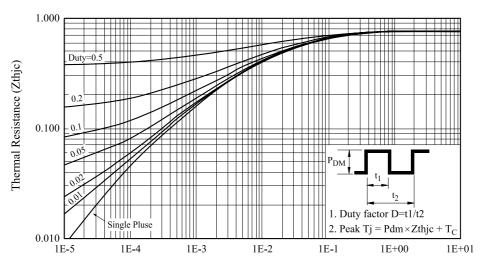
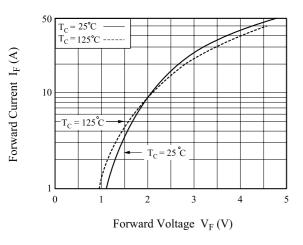


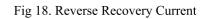
Fig 16. Transient Thermal Impedance of IGBT



Typical Performance Characteristics







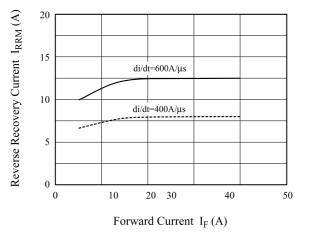
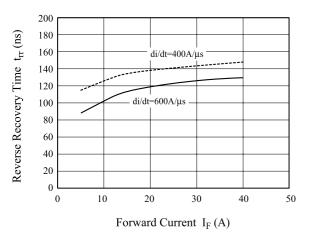


Fig 19. Reverse Recovery Time





Definition Switching Time & Loss.

Fig 20. Switching Test Circuit

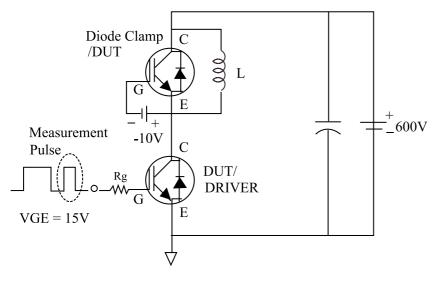


Fig 21. Definition Switching Time & Loss

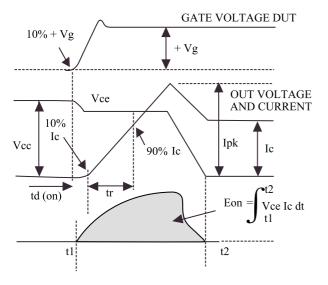
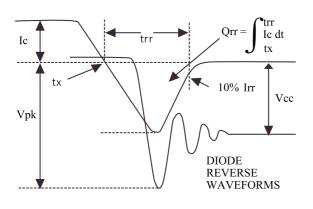
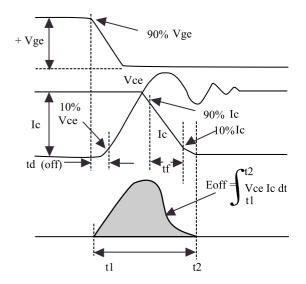


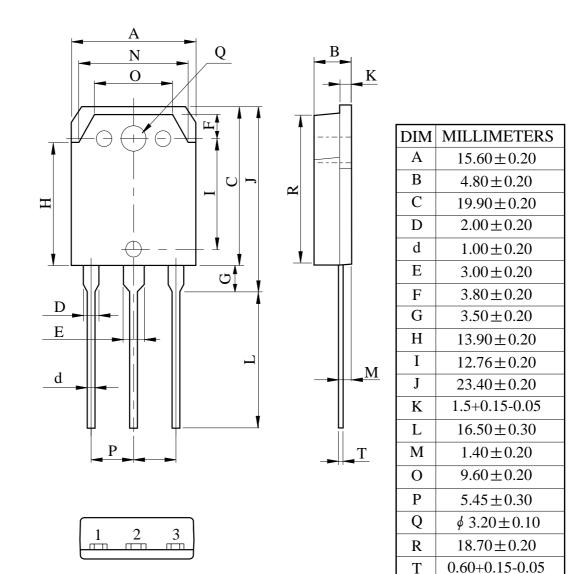
Fig 22. Definition Diode Switching Time







TO-3P (High Voltage)





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